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The invention relates to semiconductor technology and can be used, in particular, in photoelectric converters.

The process for increasing the efficiency of photovoltaic cells based on p⁺InP-p⁺InP-n⁺CdS involves the growth of the p⁺InP layer on a substrate, made in the form of a p⁺InP board with the crystallographic orientation (100), disorientation of 3...5° in the direction (110) and the charge carrier concentration of 10¹⁸ cm⁻³, deposition, on the frontal part of the board, using the method of quasi-closed volume of the n⁺CdS layer, deposition of an ohmic contact of Ag+Zn on the reverse side of the board, its thermal treatment at a temperature of 450°C, deposition of an ohmic contact of In onto the n⁺CdS layer, its thermal treatment at a temperature of 250°C and deposition by the pulverization method, at a temperature of 300°C, of a ZnO antireflection layer.

Claims: 1